

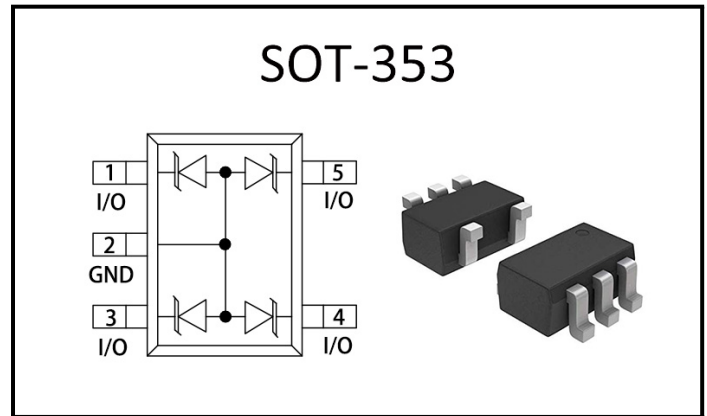
PESD5V0L4UG-N

ESD Protection Diode

Features

- 100Watts peak pulse power ($t_p = 8/20\mu s$)
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- Protection one data/power line
- IEC 61000-4-2 $\pm 30kV$ contact ; $\pm 30kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 8A (8/20 μs)

Package



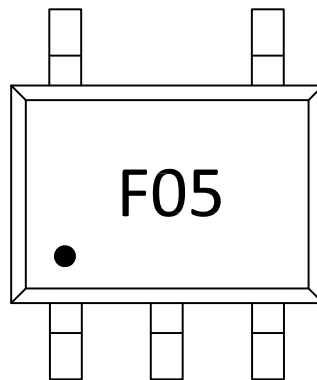
Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- SIM
- Notebook and PC Computers

Mechanical Characteristics

- SOT-353 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
PESD5V0L4UG-N	SOT-353	3k	Tape and reel

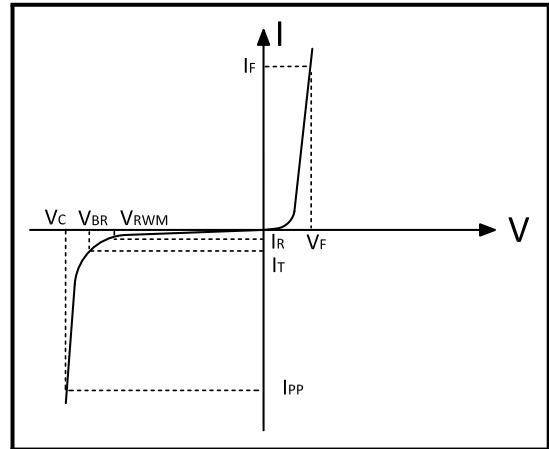


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ESD Protection Diode

Electrical Parameters ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20us pulse Waveform.

Absolute Maximum Rating

Rating	Symler	Value	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	100	Watts
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	8.0	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	30	KV
ESD per IEC 61000-4-2 (Contact)		30	
Lead Soldering Temperature	T_L	260(10seconds)	$^\circ\text{C}$
Junction Temperature	T_J	-55 to + 125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

Electrical Characteristics

Parameter	Symler	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}	–	–	–	5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	6	–	8.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5\text{V}, I_O \text{ to GND}$	–	–	0.2	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$	–	–	8.0	A
Clamping Voltage	V_C	$I_{PP} = 1.0\text{A}, t_p = 8/20\mu\text{s}, I_O \text{ to GND}$	–	–	9	V
Clamping Voltage	V_C	$I_{PP} = 8.0\text{A}, t_p = 8/20\mu\text{s}, I_O \text{ to GND}$	–	–	12	V
Junction Capacitance	C_j	$V_R = 0\text{V}, f = 1\text{MHz}, I_O \text{ to GND}$	–	60	–	pF





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Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

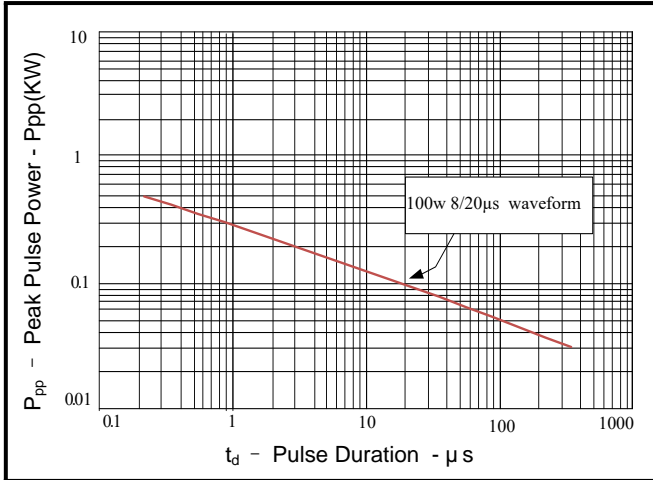


Figure 2: Power Derating Curve

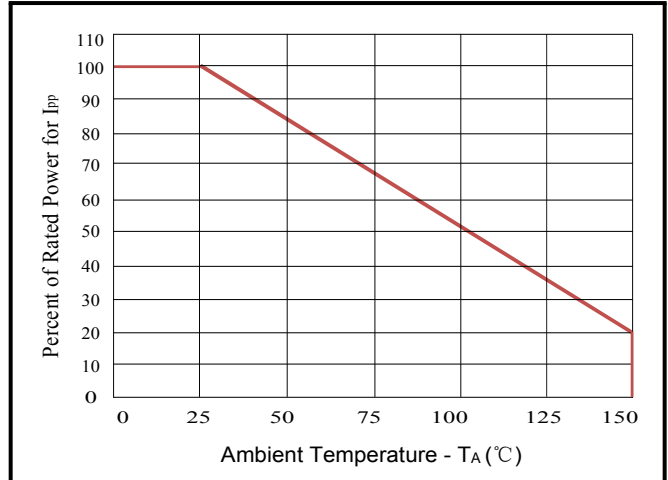


Figure 3: Pulse Waveform

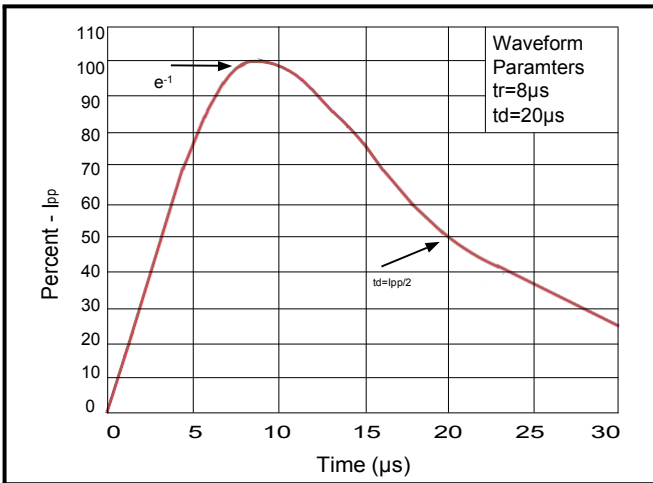
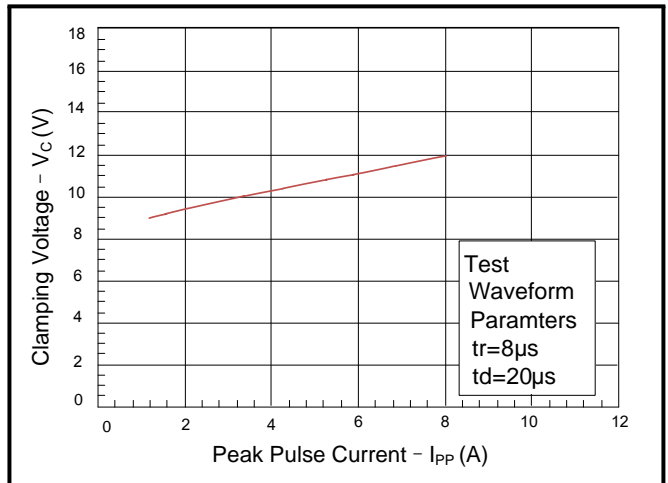


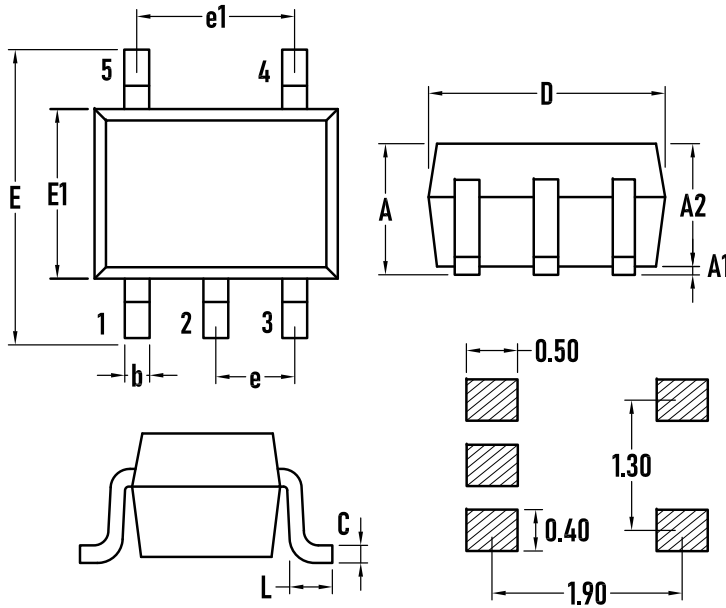
Figure 4: Clamping Voltage vs. Ipp



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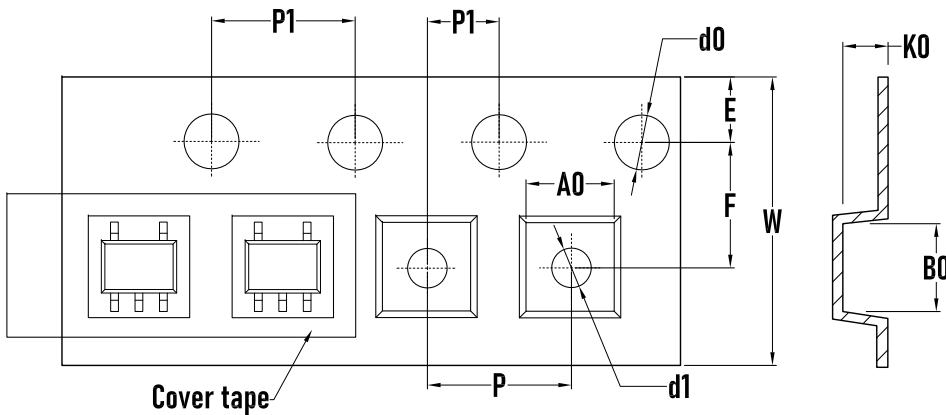
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Outline Drawing – SOT-353



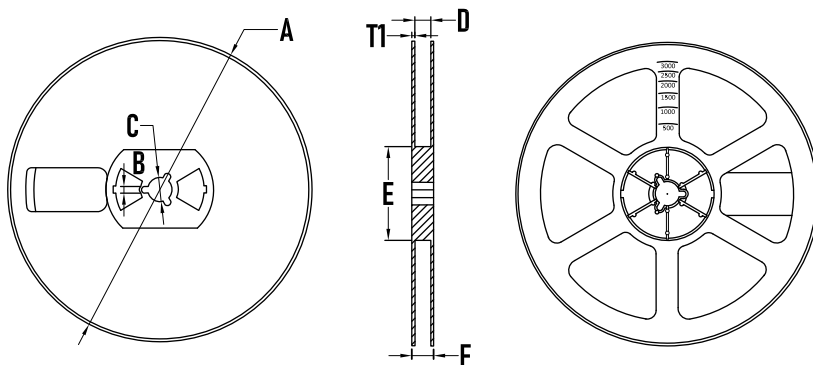
SYMBOL	MILLIMETER		
	MIN	TYP	MAX
A	0.80	0.80	1.10
A1	0.00	–	0.10
A2	0.70	0.90	1.00
b	0.15	–	0.30
C	0.08	–	0.22
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
e	0.65		
e1	1.30		
L	0.26	0.36	0.46
θ	4°		12°

Packaging Tape - SOT-353



SYMBOL	MILLIMETER
A0	2.25±0.1
B0	2.55±0.1
d0	1.50±0.1
d1	1.0±0.1
E	1.75±0.1
F	3.50±0.1
K0	1.20±0.1
P	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	8.00±0.1

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	2.7±0.2
C	13.5±0.2
D	9.6±0.3
E	54.5±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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